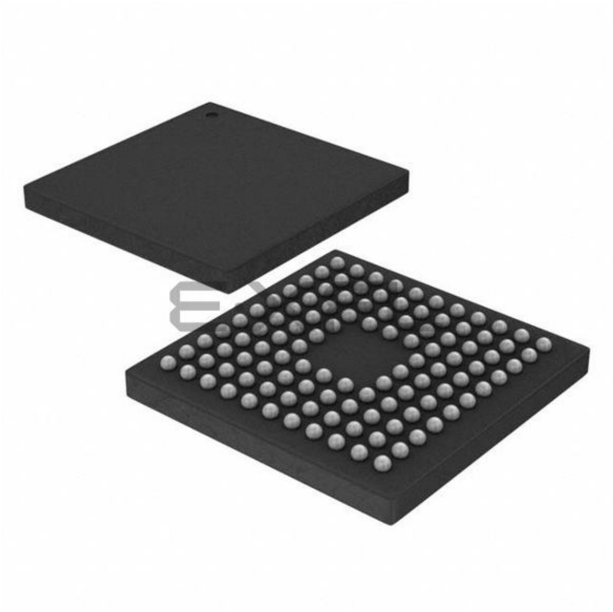


What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Discontinued at Digi-Key
Core Processor	ARM® Cortex®-M4F
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	EBI/EMI, I²C, IrDA, SmartCard, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, I²S, LCD, POR, PWM, WDT
Number of I/O	90
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.98V ~ 3.8V
Data Converters	A/D 8x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	112-LFBGA
Supplier Device Package	-
Purchase URL	https://www.e-xfl.com/product-detail/silicon-labs/efm32wg890f128-bga112t

is capable of supporting a wide range of sensors and measurement schemes, and can for instance measure LC sensors, resistive sensors and capacitive sensors. LESENSE also includes a programmable FSM which enables simple processing of measurement results without CPU intervention. LESENSE is available in energy mode EM2, in addition to EM0 and EM1, making it ideal for sensor monitoring in applications with a strict energy budget.

2.1.28 Backup Power Domain

The backup power domain is a separate power domain containing a Backup Real Time Counter, BURTC, and a set of retention registers, available in all energy modes. This power domain can be configured to automatically change power source to a backup battery when the main power drains out. The backup power domain enables the EFM32WG890 to keep track of time and retain data, even if the main power source should drain out.

2.1.29 Advanced Encryption Standard Accelerator (AES)

The AES accelerator performs AES encryption and decryption with 128-bit or 256-bit keys. Encrypting or decrypting one 128-bit data block takes 52 HFCORECLK cycles with 128-bit keys and 75 HFCORECLK cycles with 256-bit keys. The AES module is an AHB slave which enables efficient access to the data and key registers. All write accesses to the AES module must be 32-bit operations, i.e. 8- or 16-bit operations are not supported.

2.1.30 General Purpose Input/Output (GPIO)

In the EFM32WG890, there are 90 General Purpose Input/Output (GPIO) pins, which are divided into ports with up to 16 pins each. These pins can individually be configured as either an output or input. More advanced configurations like open-drain, filtering and drive strength can also be configured individually for the pins. The GPIO pins can also be overridden by peripheral pin connections, like Timer PWM outputs or USART communication, which can be routed to several locations on the device. The GPIO supports up to 16 asynchronous external pin interrupts, which enables interrupts from any pin on the device. Also, the input value of a pin can be routed through the Peripheral Reflex System to other peripherals.

2.1.31 Liquid Crystal Display Driver (LCD)

The LCD driver is capable of driving a segmented LCD display with up to 8x36 segments. A voltage boost function enables it to provide the LCD display with higher voltage than the supply voltage for the device. In addition, an animation feature can run custom animations on the LCD display without any CPU intervention. The LCD driver can also remain active even in Energy Mode 2 and provides a Frame Counter interrupt that can wake-up the device on a regular basis for updating data.

2.2 Configuration Summary

The features of the EFM32WG890 is a subset of the feature set described in the EFM32WG Reference Manual. Table 2.1 (p. 7) describes device specific implementation of the features.

Table 2.1. Configuration Summary

Module	Configuration	Pin Connections
Cortex-M4	Full configuration	NA
DBG	Full configuration	DBG_SWCLK, DBG_SWDIO, DBG_SWO
MSC	Full configuration	NA
DMA	Full configuration	NA
RMU	Full configuration	NA
EMU	Full configuration	NA

Module	Configuration	Pin Connections
CMU	Full configuration	CMU_OUT0, CMU_OUT1
WDOG	Full configuration	NA
PRS	Full configuration	NA
EBI	Full configuration	EBI_A[27:0], EBI_AD[15:0], EBI_ARDY, EBI_ALE, EBI_BL[1:0], EBI_CS[3:0], EBI_CSTFT, EBI_DCLK, EBI_DTEN, EBI_HSNC, EBI_NANDREn, EBI_NANDWEn, EBI_REn, EBI_VSNC, EBI_WEn
I2C0	Full configuration	I2C0_SDA, I2C0_SCL
I2C1	Full configuration	I2C1_SDA, I2C1_SCL
USART0	Full configuration with IrDA	US0_TX, US0_RX. US0_CLK, US0_CS
USART1	Full configuration with I2S	US1_TX, US1_RX, US1_CLK, US1_CS
USART2	Full configuration with I2S	US2_TX, US2_RX, US2_CLK, US2_CS
UART0	Full configuration	U0_TX, U0_RX
UART1	Full configuration	U1_TX, U1_RX
LEUART0	Full configuration	LEU0_TX, LEU0_RX
LEUART1	Full configuration	LEU1_TX, LEU1_RX
TIMER0	Full configuration with DTI	TIM0_CC[2:0], TIM0_CDTI[2:0]
TIMER1	Full configuration	TIM1_CC[2:0]
TIMER2	Full configuration	TIM2_CC[2:0]
TIMER3	Full configuration	TIM3_CC[2:0]
RTC	Full configuration	NA
BURTC	Full configuration	NA
LETIMER0	Full configuration	LET0_O[1:0]
PCNT0	Full configuration, 16-bit count register	PCNT0_S[1:0]
PCNT1	Full configuration, 8-bit count register	PCNT1_S[1:0]
PCNT2	Full configuration, 8-bit count register	PCNT2_S[1:0]
ACMP0	Full configuration	ACMP0_CH[7:0], ACMP0_O
ACMP1	Full configuration	ACMP1_CH[7:0], ACMP1_O
VCMP	Full configuration	NA
ADC0	Full configuration	ADC0_CH[7:0]
DAC0	Full configuration	DAC0_OUT[1:0], DAC0_OUTxALT
OPAMP	Full configuration	Outputs: OPAMP_OUTx, OPAMP_OUTxALT, Inputs: OPAMP_Px, OPAMP_Nx
AES	Full configuration	NA
GPIO	90 pins	Available pins are shown in Table 4.3 (p. 70)
LCD	Full configuration	LCD_SEG[35:0], LCD_COM[7:0], LCD_BCAP_P, LCD_BCAP_N, LCD_BEXT

3 Electrical Characteristics

3.1 Test Conditions

3.1.1 Typical Values

The typical data are based on T_{AMB}=25°C and V_{DD}=3.0 V, as defined in Table 3.2 (p. 10), by simulation and/or technology characterisation unless otherwise specified.

3.1.2 Minimum and Maximum Values

The minimum and maximum values represent the worst conditions of ambient temperature, supply voltage and frequencies, as defined in Table 3.2 (p. 10), by simulation and/or technology characterisation unless otherwise specified.

3.2 Absolute Maximum Ratings

The absolute maximum ratings are stress ratings, and functional operation under such conditions are not guaranteed. Stress beyond the limits specified in Table 3.1 (p. 10) may affect the device reliability or cause permanent damage to the device. Functional operating conditions are given in Table 3.2 (p. 10) .

Table 3.1. Absolute Maximum Ratings

Symbol	Parameter	Condition	Min	Typ	Max	Unit
T_{STG}	Storage temperature range		-40		150[1]	°C
T_S	Maximum soldering temperature	Latest IPC/JEDEC J-STD-020 Standard			260	°C
V_{DDMAX}	External main supply voltage		0		3.8	V
V_{IOPIN}	Voltage on any I/O pin		-0.3		V_{DD}+0.3	V

[1] Based on programmed devices tested for 10000 hours at 150ºC. Storage temperature affects retention of preprogrammed calibration values stored in flash. Please refer to the Flash section in the Electrical Characteristics for information on flash data retention for different temperatures.

3.3 General Operating Conditions

3.3.1 General Operating Conditions

Table 3.2. General Operating Conditions

Symbol	Parameter	Min	Typ	Max	Unit
T_{AMB}	Ambient temperature range	-40		85	°C
V_{DDOP}	Operating supply voltage	1.98		3.8	V
f_{APB}	Internal APB clock frequency			48	MHz
f_{AHB}	Internal AHB clock frequency			48	MHz

3.6 Power Management

The EFM32WG requires the AVDD_x, VDD_DREG and IOVDD_x pins to be connected together (with optional filter) at the PCB level. For practical schematic recommendations, please see the application note, "AN0002 EFM32 Hardware Design Considerations".

Table 3.6. Power Management

Symbol	Parameter	Condition	Min	Typ	Max	Unit
$V_{BODextthr-}$	BOD threshold on falling external supply voltage		1.74		1.96	V
$V_{BODextthr+}$	BOD threshold on rising external supply voltage			1.85	1.98	V
$V_{PORthr+}$	Power-on Reset (POR) threshold on rising external supply voltage				1.98	V
t_{RESET}	Delay from reset is released until program execution starts	Applies to Power-on Reset, Brown-out Reset and pin reset.		163		µs
$C_{DECOUPLE}$	Voltage regulator decoupling capacitor.	X5R capacitor recommended. Apply between DECOUPLE pin and GROUND		1		µF

3.7 Flash

Table 3.7. Flash

Symbol	Parameter	Condition	Min	Typ	Max	Unit
EC_{FLASH}	Flash erase cycles before failure		20000			cycles
RET_{FLASH}	Flash data retention	T_{AMB}<150°C	10000			h
		T_{AMB}<85°C	10			years
		T_{AMB}<70°C	20			years
t_{W_PROG}	Word (32-bit) programming time		20			µs
t_{PERASE}	Page erase time		20	20.4	20.8	ms
t_{DERASE}	Device erase time		40	40.8	41.6	ms
I_{ERASE}	Erase current				7[1]	mA
I_{WRITE}	Write current				7[1]	mA
V_{FLASH}	Supply voltage during flash erase and write		1.98		3.8	V

[1] Measured at 25°C

3.8 General Purpose Input Output

Table 3.8. GPIO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V_{IOIL}	Input low voltage				$0.30V_{DD}$	V
V_{IOIH}	Input high voltage		$0.70V_{DD}$			V
V_{IOOH}	Output high voltage (Production test condition = 3.0V, DRIVEMODE = STANDARD)	Sourcing 0.1 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		$0.80V_{DD}$		V
		Sourcing 0.1 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		$0.90V_{DD}$		V
		Sourcing 1 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = LOW		$0.85V_{DD}$		V
		Sourcing 1 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = LOW		$0.90V_{DD}$		V
		Sourcing 6 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = STANDARD	$0.75V_{DD}$			V
		Sourcing 6 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = STANDARD	$0.85V_{DD}$			V
		Sourcing 20 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = HIGH	$0.60V_{DD}$			V
		Sourcing 20 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = HIGH	$0.80V_{DD}$			V
V_{IOOL}	Output low voltage (Production test condition = 3.0V, DRIVEMODE = STANDARD)	Sinking 0.1 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		$0.20V_{DD}$		V
		Sinking 0.1 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		$0.10V_{DD}$		V
		Sinking 1 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = LOW		$0.10V_{DD}$		V
		Sinking 1 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = LOW		$0.05V_{DD}$		V
		Sinking 6 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = STANDARD			$0.30V_{DD}$	V
		Sinking 6 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = STANDARD			$0.20V_{DD}$	V
		Sinking 20 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = HIGH			$0.35V_{DD}$	V

3.9.4 HFRCO

Table 3.12. HFRCO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{HFRCO}	Oscillation frequency, V_{DD}= 3.0 V, T_{AMB}=25°C	28 MHz frequency band	27.5	28.0	28.5	MHz
		21 MHz frequency band	20.6	21.0	21.4	MHz
		14 MHz frequency band	13.7	14.0	14.3	MHz
		11 MHz frequency band	10.8	11.0	11.2	MHz
		7 MHz frequency band	6.48	6.60	6.72	MHz
		1 MHz frequency band	1.15	1.20	1.25	MHz
$t_{HFRCO\_settling}$	Settling time after start-up	f_{HFRCO} = 14 MHz		0.6		Cycles
I_{HFRCO}	Current consumption	f_{HFRCO} = 28 MHz		165	215	µA
		f_{HFRCO} = 21 MHz		134	175	µA
		f_{HFRCO} = 14 MHz		106	140	µA
		f_{HFRCO} = 11 MHz		94	125	µA
		f_{HFRCO} = 6.6 MHz		77	105	µA
		f_{HFRCO} = 1.2 MHz		25	40	µA
DC_{HFRCO}	Duty cycle	f_{HFRCO} = 14 MHz	48.5	50	51	%
$TUNESTEP_{HFRCO}$	Frequency step for LSB change in TUNING value			0.3[1]		%

[1] The TUNING field in the CMU_HFRCOCTRL register may be used to adjust the HFRCO frequency. There is enough adjustment range to ensure that the frequency bands above 7 MHz will always have some overlap across supply voltage and temperature. By using a stable frequency reference such as the LFXO or HFXO, a firmware calibration routine can vary the TUNING bits and the frequency band to maintain the HFRCO frequency at any arbitrary value between 7 MHz and 28 MHz across operating conditions.

Figure 3.18. Calibrated HFRCO 1 MHz Band Frequency vs Supply Voltage and Temperature

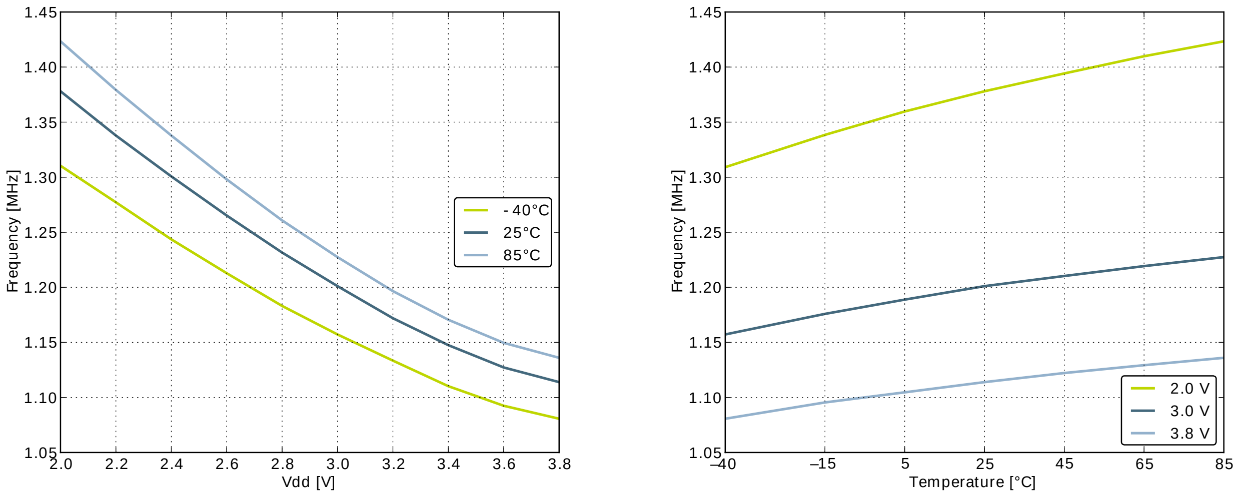


Figure 3.22. Calibrated HFRCO 21 MHz Band Frequency vs Supply Voltage and Temperature

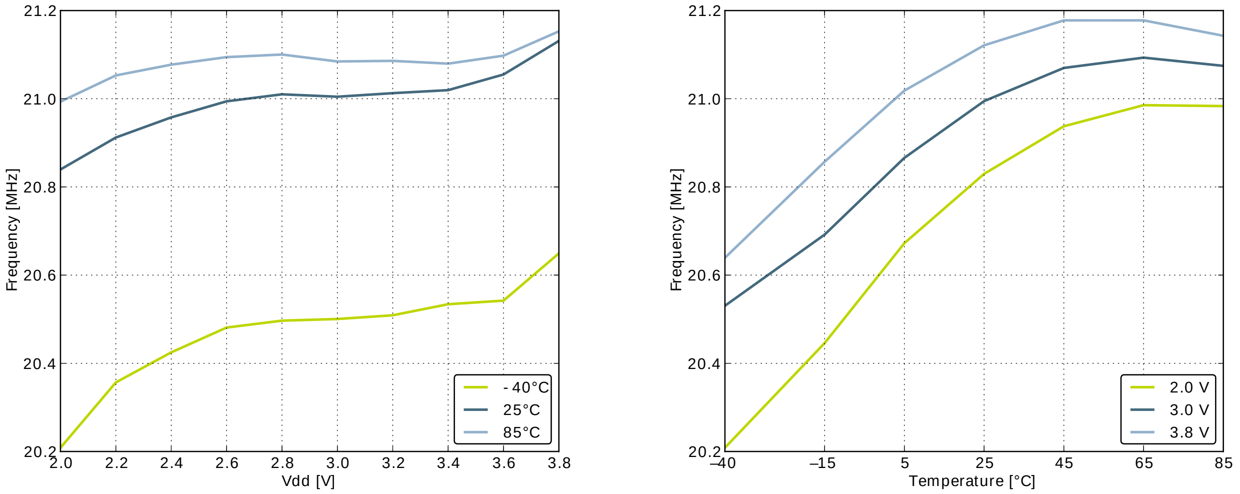
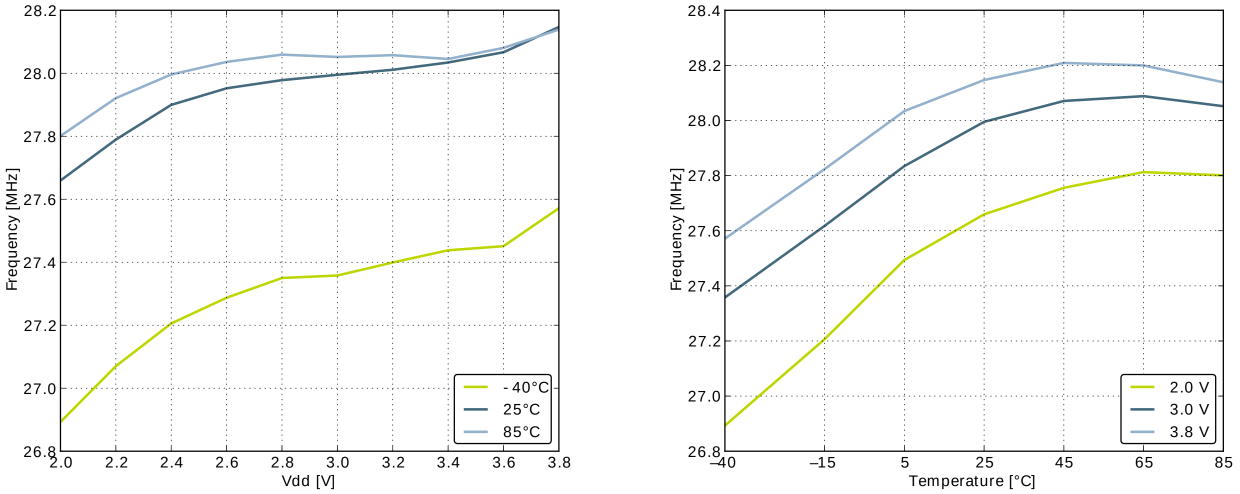
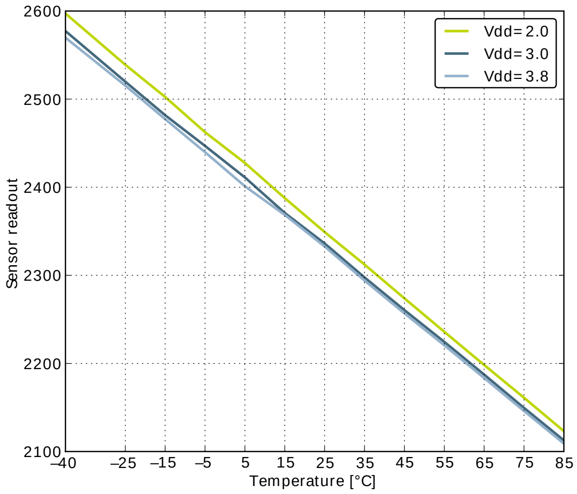


Figure 3.23. Calibrated HFRCO 28 MHz Band Frequency vs Supply Voltage and Temperature



Symbol	Parameter	Condition	Min	Typ	Max	Unit
	and ADC core in NORMAL mode					
	Startup time of reference generator and ADC core in KEEPADCWARM mode			1		µs
SNR_{ADC}	Signal to Noise Ratio (SNR)	1 MSamples/s, 12 bit, single ended, internal 1.25V reference		59		dB
		1 MSamples/s, 12 bit, single ended, internal 2.5V reference		63		dB
		1 MSamples/s, 12 bit, single ended, V_{DD} reference		65		dB
		1 MSamples/s, 12 bit, differential, internal 1.25V reference		60		dB
		1 MSamples/s, 12 bit, differential, internal 2.5V reference		65		dB
		1 MSamples/s, 12 bit, differential, 5V reference		54		dB
		1 MSamples/s, 12 bit, differential, V_{DD} reference		67		dB
		1 MSamples/s, 12 bit, differential, $2xV_{DD}$ reference		69		dB
		200 kSamples/s, 12 bit, single ended, internal 1.25V reference		62		dB
		200 kSamples/s, 12 bit, single ended, internal 2.5V reference		63		dB
		200 kSamples/s, 12 bit, single ended, V_{DD} reference		67		dB
		200 kSamples/s, 12 bit, differential, internal 1.25V reference		63		dB
		200 kSamples/s, 12 bit, differential, internal 2.5V reference		66		dB
		200 kSamples/s, 12 bit, differential, 5V reference		66		dB
		200 kSamples/s, 12 bit, differential, V_{DD} reference	63	66		dB
		200 kSamples/s, 12 bit, differential, $2xV_{DD}$ reference		70		dB
$SINAD_{ADC}$	SIgnal-to-Noise And Distortion-ratio (SINAD)	1 MSamples/s, 12 bit, single ended, internal 1.25V reference		58		dB
		1 MSamples/s, 12 bit, single ended, internal 2.5V reference		62		dB
		1 MSamples/s, 12 bit, single ended, V_{DD} reference		64		dB
		1 MSamples/s, 12 bit, differential, internal 1.25V reference		60		dB

Figure 3.31. ADC Temperature sensor readout



3.11 Digital Analog Converter (DAC)

Table 3.16. DAC

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V_{DACOUT}	Output voltage range	VDD voltage reference, single ended	0		V_{DD}	V
		VDD voltage reference, differential	$-V_{DD}$		V_{DD}	V
V_{DACCM}	Output common mode voltage range		0		V_{DD}	V
I_{DAC}	Active current including references for 2 channels	500 kSamples/s, 12 bit		400[1]		µA
		100 kSamples/s, 12 bit		200[1]		µA
		1 kSamples/s 12 bit NORMAL		17[1]		µA
SR_{DAC}	Sample rate				500	ksamples/s
f_{DAC}	DAC clock frequency	Continuous Mode			1000	kHz
		Sample/Hold Mode			250	kHz
		Sample/Off Mode			250	kHz
$CYC_{DACCONV}$	Clock cyckles per conversion			2		
$t_{DACCONV}$	Conversion time		2			µs
$t_{DACSETTLE}$	Settling time			5		µs
SNR_{DAC}	Signal to Noise Ratio (SNR)	500 kSamples/s, 12 bit, single ended, internal 1.25V reference		58		dB
		500 kSamples/s, 12 bit, single ended, internal 2.5V reference		59		dB
		500 kSamples/s, 12 bit, differential, internal 1.25V reference		58		dB

Symbol	Parameter	Condition	Min	Typ	Max	Unit
		500 kSamples/s, 12 bit, differential, internal 2.5V reference		58		dB
		500 kSamples/s, 12 bit, differential, V_{DD} reference		59		dB
$SNDR_{DAC}$	Signal to Noise-pulse Distortion Ratio (SNDR)	500 kSamples/s, 12 bit, single ended, internal 1.25V reference		57		dB
		500 kSamples/s, 12 bit, single ended, internal 2.5V reference		54		dB
		500 kSamples/s, 12 bit, differential, internal 1.25V reference		56		dB
		500 kSamples/s, 12 bit, differential, internal 2.5V reference		53		dB
		500 kSamples/s, 12 bit, differential, V_{DD} reference		55		dB
$SFDR_{DAC}$	Spurious-Free Dynamic Range(SFDR)	500 kSamples/s, 12 bit, single ended, internal 1.25V reference		62		dBc
		500 kSamples/s, 12 bit, single ended, internal 2.5V reference		56		dBc
		500 kSamples/s, 12 bit, differential, internal 1.25V reference		61		dBc
		500 kSamples/s, 12 bit, differential, internal 2.5V reference		55		dBc
		500 kSamples/s, 12 bit, differential, V_{DD} reference		60		dBc
$V_{DACOFFSET}$	Offset voltage	After calibration, single ended		2	9	mV
		After calibration, differential		2		mV
DNL_{DAC}	Differential non-linearity			±1		LSB
INL_{DAC}	Integral non-linearity			±5		LSB
MC_{DAC}	No missing codes			12		bits

[1] Measured with a static input code and no loading on the output.

3.12 Operational Amplifier (OPAMP)

The electrical characteristics for the Operational Amplifiers are based on simulations.

Table 3.17. OPAMP

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I_{OPAMP}	Active Current	(OPA2)BIASPROG=0xF, (OPA2)HALFBIAS=0x0, Unity Gain		370	460	µA
		(OPA2)BIASPROG=0x7, (OPA2)HALFBIAS=0x1, Unity Gain		95	135	µA

3.13 Analog Comparator (ACMP)

Table 3.18. ACMP

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V_{ACMPIN}	Input voltage range		0		V_{DD}	V
V_{ACMPCM}	ACMP Common Mode voltage range		0		V_{DD}	V
I_{ACMP}	Active current	BIASPROG=0b0000, FULLBIAS=0 and HALFBIAS=1 in ACMPn_CTRL register		0.1	0.4	µA
		BIASPROG=0b1111, FULLBIAS=0 and HALFBIAS=0 in ACMPn_CTRL register		2.87	15	µA
		BIASPROG=0b1111, FULLBIAS=1 and HALFBIAS=0 in ACMPn_CTRL register		195	520	µA
$I_{ACMPREF}$	Current consumption of internal voltage reference	Internal voltage reference off. Using external voltage reference		0		µA
		Internal voltage reference		5		µA
$V_{ACMPOFFSET}$	Offset voltage	BIASPROG= 0b1010, FULLBIAS=0 and HALFBIAS=0 in ACMPn_CTRL register	-12	0	12	mV
$V_{ACMPHYST}$	ACMP hysteresis	Programmable		17		mV
R_{CSRES}	Capacitive Sense Internal Resistance	CSRESSEL=0b00 in ACMPn_INPUTSEL		39		kOhm
		CSRESSEL=0b01 in ACMPn_INPUTSEL		71		kOhm
		CSRESSEL=0b10 in ACMPn_INPUTSEL		104		kOhm
		CSRESSEL=0b11 in ACMPn_INPUTSEL		136		kOhm
$t_{ACMPSTART}$	Startup time				10	µs

The total ACMP current is the sum of the contributions from the ACMP and its internal voltage reference as given in Equation 3.1 (p. 47) . $I_{ACMPREF}$ is zero if an external voltage reference is used.

Total ACMP Active Current

$$I_{ACMPTOTAL} = I_{ACMP} + I_{ACMPREF} \tag{3.1}$$

Table 3.20. EBI Write Enable Timing

Symbol	Parameter	Min	Typ	Max	Unit
t_{OH_WEn} [1, 2, 3, 4]	Output hold time, from trailing EBI_WEn/ EBI_NANDWEn edge to EBI_AD, EBI_A, EBI_CSn, EBI_BLn invalid	-6.00 + (WRHOLD * $t_{HFCORECLK}$)			ns
t_{OSU_WEn} [1, 2, 3, 4, 5]	Output setup time, from EBI_AD, EBI_A, EBI_CSn, EBI_BLn valid to leading EBI_WEn/ EBI_NANDWEn edge	-14.00 + (WRSETUP * $t_{HFCORECLK}$)			ns
t_{WIDTH_WEn} [1, 2, 3, 4, 5]	EBI_WEn/EBI_NANDWEn pulse width	-7.00 + ((WRSTRB +1) * $t_{HFCORECLK}$)			ns

[1] Applies for all addressing modes (figure only shows D16 addressing mode)

[2] Applies for both EBI_WEn and EBI_NANWEn (figure only shows EBI_WEn)

[3] Applies for all polarities (figure only shows active low signals)

[4] Measurement done at 10% and 90% of V_{DD} (figure shows 50% of $_{VDD}$)

[5] The figure shows the timing for the case that the half strobe length functionality is not used, i.e. HALFWE=0. The leading edge of EBI_WEn can be moved to the right by setting HALFWE=1. This decreases the length of t_{WIDTH_WEn} and increases the length of t_{OSU_WEn} by 1/2 * $t_{HFCLKNODIV}$.

Figure 3.39. EBI Address Latch Enable Related Output Timing

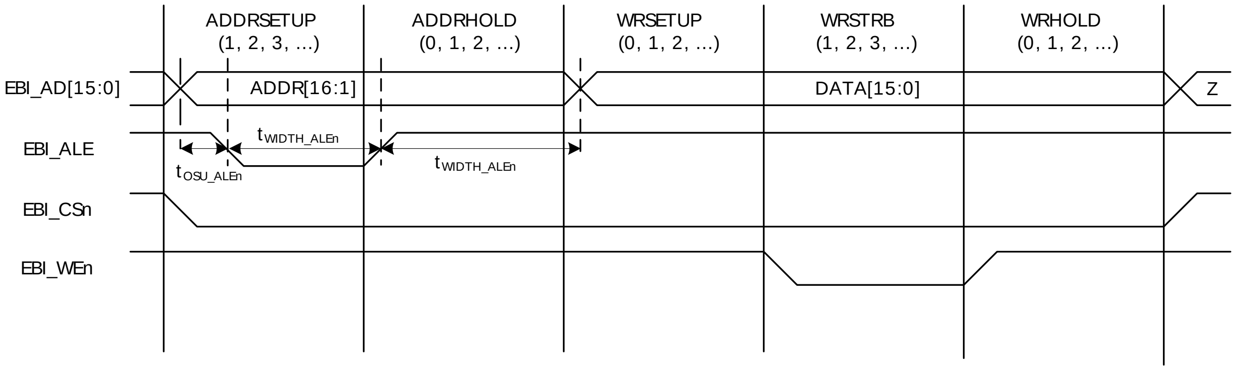


Table 3.21. EBI Address Latch Enable Related Output Timing

Symbol	Parameter	Min	Typ	Max	Unit
t_{OH_ALEn} [1, 2, 3, 4]	Output hold time, from trailing EBI_ALE edge to EBI_AD invalid	-6.00 + (ADDRHOLD[5] * $t_{HFCORECLK}$)			ns
t_{OSU_ALEn} [1, 2, 4]	Output setup time, from EBI_AD valid to leading EBI_ALE edge	-13.00 + (0 * $t_{HFCORECLK}$)			ns
t_{WIDTH_ALEn} [1, 2, 3, 4]	EBI_ALEn pulse width	-7.00 + (ADDRSETUP+1) * $t_{HFCORECLK}$)			ns

[1] Applies to addressing modes D8A24ALE and D16A16ALE (figure only shows D16A16ALE)

[2] Applies for all polarities (figure only shows active low signals)

[3] The figure shows the timing for the case that the half strobe length functionality is not used, i.e. HALFALE=0. The trailing edge of EBI_ALE can be moved to the left by setting HALFALE=1. This decreases the length of t_{WIDTH_ALEn} and increases the length of tOH_ALEn by $t_{HFCORECLK}$ - 1/2 * $t_{HFCLKNODIV}$.

[4] Measurement done at 10% and 90% of V_{DD} (figure shows 50% of $_{VDD}$)

[5] Figure only shows a write operation. For a multiplexed read operation the address hold time is controlled via the RDSETUP state instead of via the ADDRHOLD state.

Figure 3.41. EBI Read Enable Related Timing Requirements

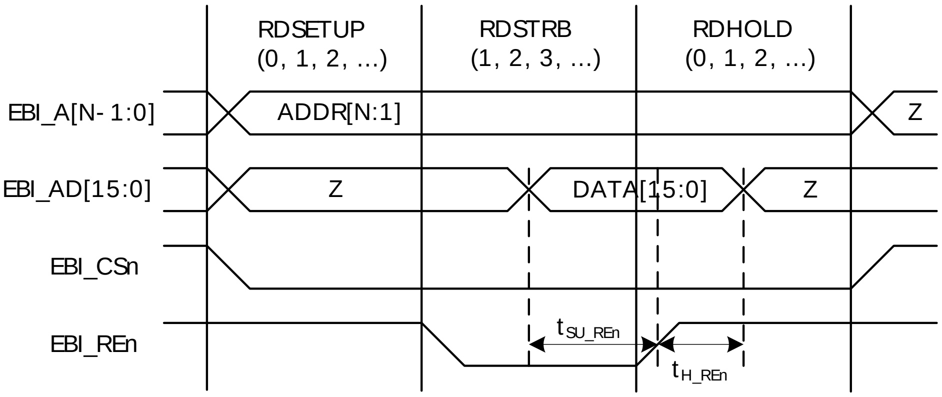


Table 3.23. EBI Read Enable Related Timing Requirements

Symbol	Parameter	Min	Typ	Max	Unit
t_{SU_REn} [1 2 3 4]	Setup time, from EBI_AD valid to trailing EBI_REn edge	37			ns
t_{H_Ren} [1 2 3 4]	Hold time, from trailing EBI_REn edge to EBI_AD invalid	-1			ns

[1] Applies for all addressing modes (figure only shows D16A8).

[2] Applies for both EBI_REn and EBI_NANDREn (figure only shows EBI_REn)

[3] Applies for all polarities (figure only shows active low signals)

[4] Measurement done at 10% and 90% of V_{DD} (figure shows 50% of $_{VDD}$)

Figure 3.42. EBI Ready/Wait Related Timing Requirements

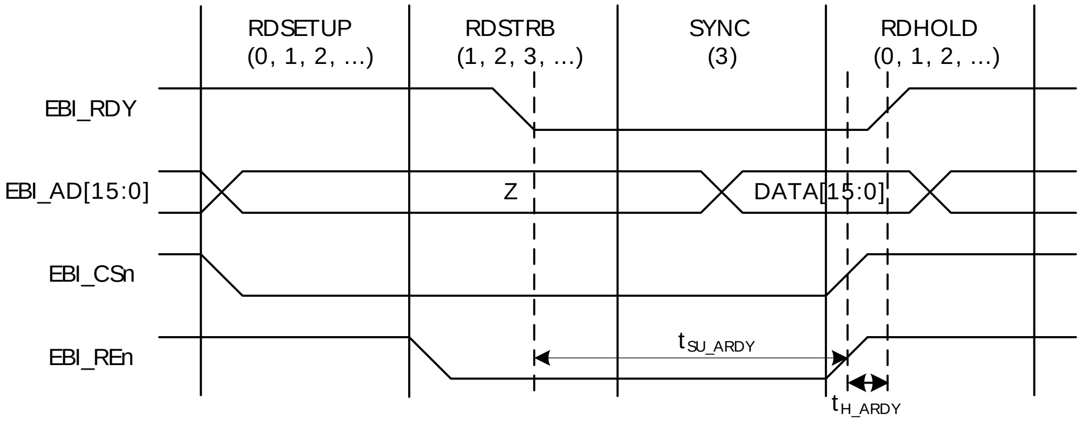


Table 3.24. EBI Ready/Wait Related Timing Requirements

Symbol	Parameter	Min	Typ	Max	Unit
t_{SU_ARDY} [1 2 3 4]	Setup time, from EBI_ARDY valid to trailing EBI_REn, EBI_WEn edge	37 + (3 * $t_{HFCORECLK}$)			ns

3.17 I2C

Table 3.26. I2C Standard-mode (Sm)

Symbol	Parameter	Min	Typ	Max	Unit
f_{SCL}	SCL clock frequency	0		100[1]	kHz
t_{LOW}	SCL clock low time	4.7			µs
t_{HIGH}	SCL clock high time	4.0			µs
$t_{SU,DAT}$	SDA set-up time	250			ns
$t_{HD,DAT}$	SDA hold time	8		3450[2,3]	ns
$t_{SU,STA}$	Repeated START condition set-up time	4.7			µs
$t_{HD,STA}$	(Repeated) START condition hold time	4.0			µs
$t_{SU,STO}$	STOP condition set-up time	4.0			µs
t_{BUF}	Bus free time between a STOP and a START condition	4.7			µs

[1] For the minimum HFPERCLK frequency required in Standard-mode, see the I2C chapter in the EFM32WG Reference Manual.

[2] The maximum SDA hold time ($t_{HD,DAT}$) needs to be met only when the device does not stretch the low time of SCL (t_{LOW}).

[3] When transmitting data, this number is guaranteed only when I2Cn_CLKDIV < $((3450*10^{-9}$ [s] $* f_{HFPERCLK}$ [Hz]) - 4).

Table 3.27. I2C Fast-mode (Fm)

Symbol	Parameter	Min	Typ	Max	Unit
f_{SCL}	SCL clock frequency	0		400[1]	kHz
t_{LOW}	SCL clock low time	1.3			µs
t_{HIGH}	SCL clock high time	0.6			µs
$t_{SU,DAT}$	SDA set-up time	100			ns
$t_{HD,DAT}$	SDA hold time	8		900[2,3]	ns
$t_{SU,STA}$	Repeated START condition set-up time	0.6			µs
$t_{HD,STA}$	(Repeated) START condition hold time	0.6			µs
$t_{SU,STO}$	STOP condition set-up time	0.6			µs
t_{BUF}	Bus free time between a STOP and a START condition	1.3			µs

[1] For the minimum HFPERCLK frequency required in Fast-mode, see the I2C chapter in the EFM32WG Reference Manual.

[2] The maximum SDA hold time ($t_{HD,DAT}$) needs to be met only when the device does not stretch the low time of SCL (t_{LOW}).

[3] When transmitting data, this number is guaranteed only when I2Cn_CLKDIV < $((900*10^{-9}$ [s] $* f_{HFPERCLK}$ [Hz]) - 4).

Table 3.28. I2C Fast-mode Plus (Fm+)

Symbol	Parameter	Min	Typ	Max	Unit
f_{SCL}	SCL clock frequency	0		1000[1]	kHz
t_{LOW}	SCL clock low time	0.5			µs
t_{HIGH}	SCL clock high time	0.26			µs
$t_{SU,DAT}$	SDA set-up time	50			ns
$t_{HD,DAT}$	SDA hold time	8			ns
$t_{SU,STA}$	Repeated START condition set-up time	0.26			µs
$t_{HD,STA}$	(Repeated) START condition hold time	0.26			µs
$t_{SU,STO}$	STOP condition set-up time	0.26			µs
t_{BUF}	Bus free time between a STOP and a START condition	0.5			µs

[1] For the minimum HFPERCLK frequency required in Fast-mode Plus, see the I2C chapter in the EFM32WG Reference Manual.

3.18 USART SPI

Figure 3.43. SPI Master Timing

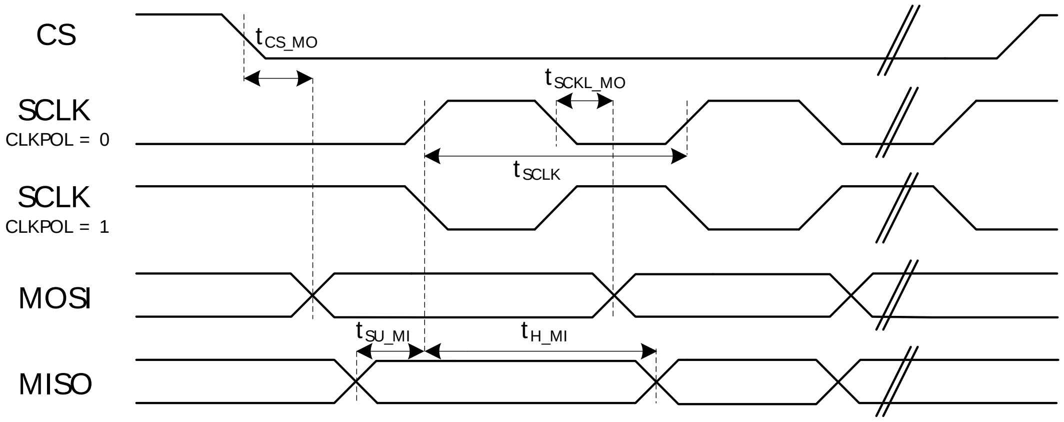


Table 3.29. SPI Master Timing

Symbol	Parameter	Condition	Min	Typ	Max	Unit
t_{SCLK} [1] [2]	SCLK period		2 * $t_{HFPERCLK}$			ns
t_{CS_MO} [1] [2]	CS to MOSI		-2.00		2.00	ns
t_{SCLK_MO} [1] [2]	SCLK to MOSI		-1.00		3.00	ns
t_{SU_MI} [1] [2]	MISO setup time	IOVDD = 3.0 V	36.00			ns
t_{H_MI} [1] [2]	MISO hold time		-6.00			ns

[1] Applies for both CLKPHA = 0 and CLKPHA = 1 (figure only shows CLKPHA = 0)

[2] Measurement done at 10% and 90% of V_{DD} (figure shows 50% of V_{DD})

Alternate	LOCATION							
Functionality	0	1	2	3	4	5	6	Description
OPAMP_OUT2	PD5	PD0						Operational Amplifier 2 output.
DAC0_P0 / OPAMP_P0	PC4							Operational Amplifier 0 external positive input.
DAC0_P1 / OPAMP_P1	PD6							Operational Amplifier 1 external positive input.
OPAMP_P2	PD4							Operational Amplifier 2 external positive input.
DBG_SWCLK	PF0	PF0	PF0	PF0				Debug-interface Serial Wire clock input. Note that this function is enabled to pin out of reset, and has a built-in pull down.
DBG_SWDIO	PF1	PF1	PF1	PF1				Debug-interface Serial Wire data input / output. Note that this function is enabled to pin out of reset, and has a built-in pull up.
DBG_SWO	PF2	PC15	PD1	PD2				Debug-interface Serial Wire viewer Output. Note that this function is not enabled after reset, and must be enabled by software to be used.
EBI_A00	PA12	PA12	PA12					External Bus Interface (EBI) address output pin 00.
EBI_A01	PA13	PA13	PA13					External Bus Interface (EBI) address output pin 01.
EBI_A02	PA14	PA14	PA14					External Bus Interface (EBI) address output pin 02.
EBI_A03	PB9	PB9	PB9					External Bus Interface (EBI) address output pin 03.
EBI_A04	PB10	PB10	PB10					External Bus Interface (EBI) address output pin 04.
EBI_A05	PC6	PC6	PC6					External Bus Interface (EBI) address output pin 05.
EBI_A06	PC7	PC7	PC7					External Bus Interface (EBI) address output pin 06.
EBI_A07	PE0	PE0	PE0					External Bus Interface (EBI) address output pin 07.
EBI_A08	PE1	PE1	PE1					External Bus Interface (EBI) address output pin 08.
EBI_A09	PE2	PC9	PC9					External Bus Interface (EBI) address output pin 09.
EBI_A10	PE3	PC10	PC10					External Bus Interface (EBI) address output pin 10.
EBI_A11	PE4	PE4	PE4					External Bus Interface (EBI) address output pin 11.
EBI_A12	PE5	PE5	PE5					External Bus Interface (EBI) address output pin 12.
EBI_A13	PE6	PE6	PE6					External Bus Interface (EBI) address output pin 13.
EBI_A14	PE7	PE7	PE7					External Bus Interface (EBI) address output pin 14.
EBI_A15	PC8	PC8	PC8					External Bus Interface (EBI) address output pin 15.
EBI_A16	PB0	PB0	PB0					External Bus Interface (EBI) address output pin 16.
EBI_A17	PB1	PB1	PB1					External Bus Interface (EBI) address output pin 17.
EBI_A18	PB2	PB2	PB2					External Bus Interface (EBI) address output pin 18.
EBI_A19	PB3	PB3	PB3					External Bus Interface (EBI) address output pin 19.
EBI_A20	PB4	PB4	PB4					External Bus Interface (EBI) address output pin 20.
EBI_A21	PB5	PB5	PB5					External Bus Interface (EBI) address output pin 21.
EBI_A22	PB6	PB6	PB6					External Bus Interface (EBI) address output pin 22.
EBI_A23	PC0	PC0	PC0					External Bus Interface (EBI) address output pin 23.
EBI_A24	PC1	PC1	PC1					External Bus Interface (EBI) address output pin 24.
EBI_A25	PC2	PC2	PC2					External Bus Interface (EBI) address output pin 25.
EBI_A26	PC4	PC4	PC4					External Bus Interface (EBI) address output pin 26.
EBI_A27	PD2	PD2	PD2					External Bus Interface (EBI) address output pin 27.
EBI_AD00	PE8	PE8	PE8					External Bus Interface (EBI) address and data input / output pin 00.

Alternate	LOCATION							
Functionality	0	1	2	3	4	5	6	Description
LCD_SEG8	PE12							LCD segment line 8. Segments 8, 9, 10 and 11 are controlled by SEGEN2.
LCD_SEG9	PE13							LCD segment line 9. Segments 8, 9, 10 and 11 are controlled by SEGEN2.
LCD_SEG10	PE14							LCD segment line 10. Segments 8, 9, 10 and 11 are controlled by SEGEN2.
LCD_SEG11	PE15							LCD segment line 11. Segments 8, 9, 10 and 11 are controlled by SEGEN2.
LCD_SEG12	PA15							LCD segment line 12. Segments 12, 13, 14 and 15 are controlled by SEGEN3.
LCD_SEG13	PA0							LCD segment line 13. Segments 12, 13, 14 and 15 are controlled by SEGEN3.
LCD_SEG14	PA1							LCD segment line 14. Segments 12, 13, 14 and 15 are controlled by SEGEN3.
LCD_SEG15	PA2							LCD segment line 15. Segments 12, 13, 14 and 15 are controlled by SEGEN3.
LCD_SEG16	PA3							LCD segment line 16. Segments 16, 17, 18 and 19 are controlled by SEGEN4.
LCD_SEG17	PA4							LCD segment line 17. Segments 16, 17, 18 and 19 are controlled by SEGEN4.
LCD_SEG18	PA5							LCD segment line 18. Segments 16, 17, 18 and 19 are controlled by SEGEN4.
LCD_SEG19	PA6							LCD segment line 19. Segments 16, 17, 18 and 19 are controlled by SEGEN4.
LCD_SEG20/ LCD_COM4	PB3							LCD segment line 20. Segments 20, 21, 22 and 23 are controlled by SEGEN5. This pin may also be used as LCD COM line 4
LCD_SEG21/ LCD_COM5	PB4							LCD segment line 21. Segments 20, 21, 22 and 23 are controlled by SEGEN5. This pin may also be used as LCD COM line 5
LCD_SEG22/ LCD_COM6	PB5							LCD segment line 22. Segments 20, 21, 22 and 23 are controlled by SEGEN5. This pin may also be used as LCD COM line 6
LCD_SEG23/ LCD_COM7	PB6							LCD segment line 23. Segments 20, 21, 22 and 23 are controlled by SEGEN5. This pin may also be used as LCD COM line 7
LCD_SEG24	PF6							LCD segment line 24. Segments 24, 25, 26 and 27 are controlled by SEGEN6.
LCD_SEG25	PF7							LCD segment line 25. Segments 24, 25, 26 and 27 are controlled by SEGEN6.
LCD_SEG26	PF8							LCD segment line 26. Segments 24, 25, 26 and 27 are controlled by SEGEN6.
LCD_SEG27	PF9							LCD segment line 27. Segments 24, 25, 26 and 27 are controlled by SEGEN6.
LCD_SEG28	PD9							LCD segment line 28. Segments 28, 29, 30 and 31 are controlled by SEGEN7.
LCD_SEG29	PD10							LCD segment line 29. Segments 28, 29, 30 and 31 are controlled by SEGEN7.
LCD_SEG30	PD11							LCD segment line 30. Segments 28, 29, 30 and 31 are controlled by SEGEN7.
LCD_SEG31	PD12							LCD segment line 31. Segments 28, 29, 30 and 31 are controlled by SEGEN7.
LCD_SEG32	PB0							LCD segment line 32. Segments 32, 33, 34 and 35 are controlled by SEGEN8.
LCD_SEG33	PB1							LCD segment line 33. Segments 32, 33, 34 and 35 are controlled by SEGEN8.

The BGA112 Package uses SAC105 solderballs.

All EFM32 packages are RoHS compliant and free of Bromine (Br) and Antimony (Sb).

For additional Quality and Environmental information, please see:
http://www.silabs.com/support/quality/pages/default.aspx

7 Revision History

7.1 Revision 1.40

June 13th, 2014

Removed "Preliminary" markings.

Corrected single power supply voltage minimum value from 1.85V to 1.98V.

Added AUXHFRCO to blockdiagram and electrical characteristics.

Updated current consumption data.

Updated transition between energy modes data.

Updated power management data.

Updated GPIO data.

Updated LFRCO, HFRCO and ULFRCO data.

Updated ADC data.

Updated DAC data.

Updated OPAMP data.

Updated ACMP data.

Updated VCMP data.

Added EBI timing chapter.

7.2 Revision 1.31

November 21st, 2013

Updated figures.

Updated errata-link.

Updated chip marking.

Added link to Environmental and Quality information.

Re-added missing DAC-data.

7.3 Revision 1.30

September 30th, 2013

Added I2C characterization data.

Added SPI characterization data.

Corrected the DAC and OPAMP2 pin sharing information in the Alternate Functionality Pinout section.

Corrected the ADC resolution from 12, 10 and 6 bit to 12, 8 and 6 bit.

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